

Silicon PNP Power Transistors

2SA1135

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC2665

APPLICATIONS

- For general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

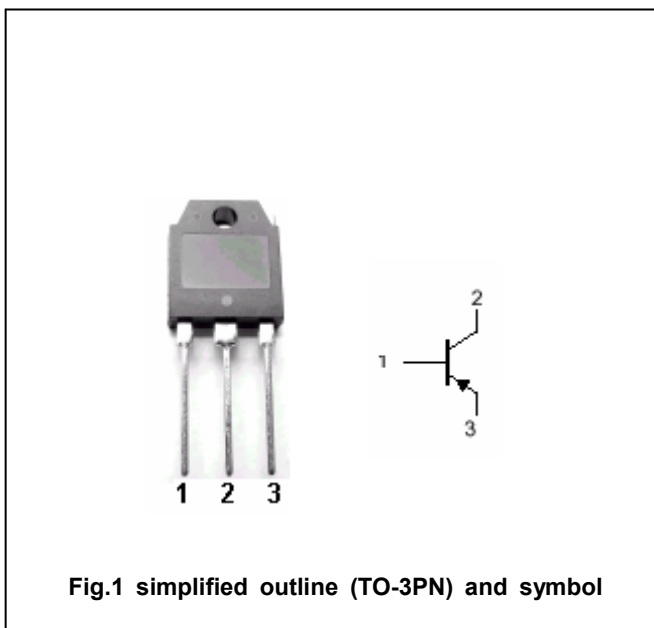


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-80	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-4	A
I _B	Base current		-1	A
P _C	Collector power dissipation	T _C =25□	55	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-80V; I _E =0			-1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-1.0	mA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-4V	40			
f _T	Transition frequency	I _E =0.2A ; V _{CE} =-10V		10		MHz

Switching times

t _r	Rise time	I _C =-2A ; V _{CC} =-6V I _{B1} =-I _{B2} =-0.3A; R _L =3Ω		1.0		μs
t _{stg}	Storage time			0.4		μs
t _f	Fall time			0.15		μs

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PACKAGE OUTLINE

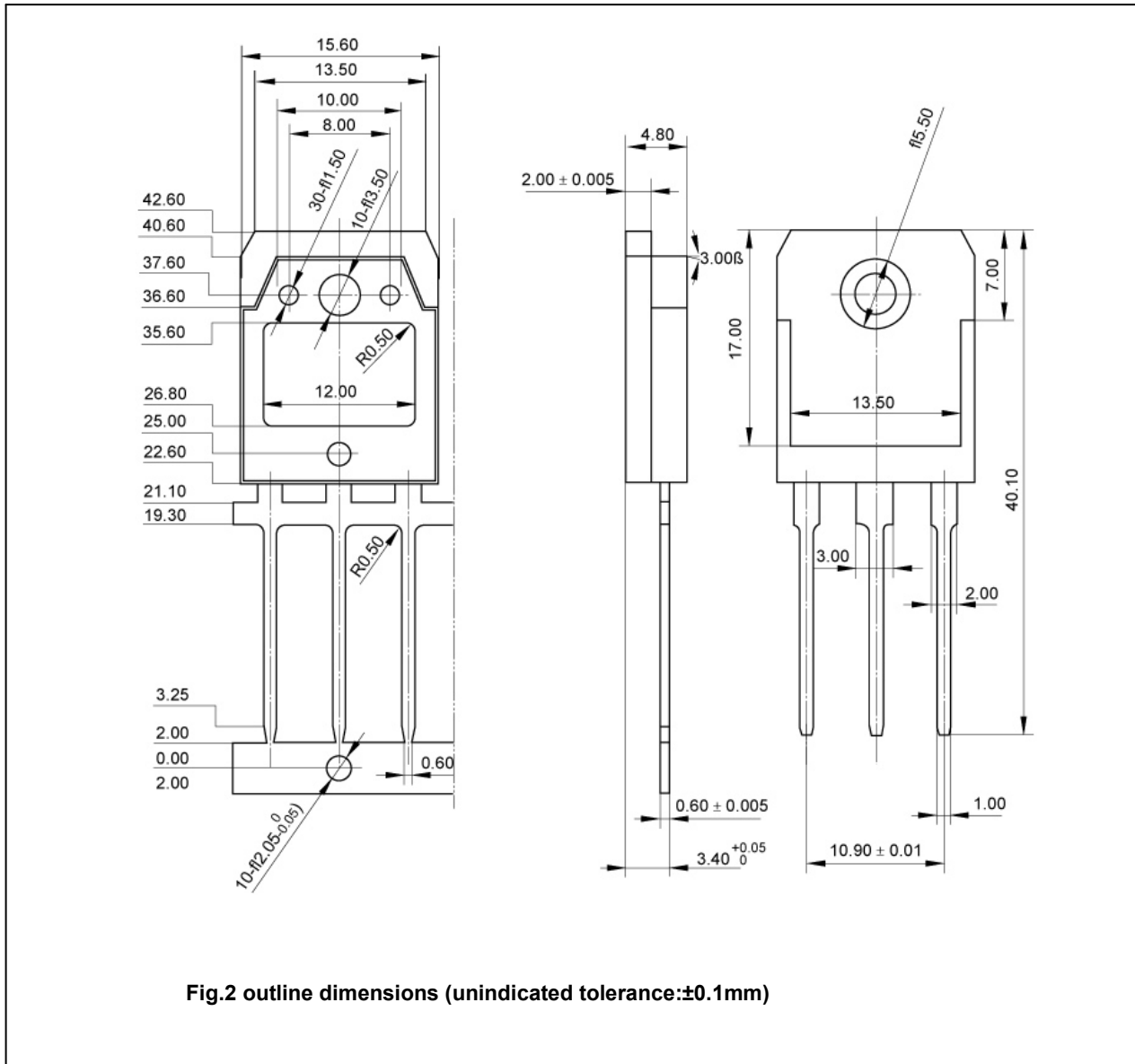


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)